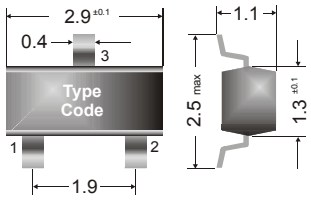
NPN

Surface mount Si-Epitaxial PlanarTransistors
Si-Epitaxial PlanarTransistoren für die Oberflächenmontage

NPN



Dimensions / Maße in mm
1 = B 2 = E 3 = C

Power dissipation – Verlustleistung 250 mW

Plastic case SOT-23
Kunststoffgehäuse (TO-236)

Weight approx. – Gewicht ca. 0.01 g

Plastic material has UL classification 94V-0
Gehäusematerial UL94V-0 klassifiziert

Standard packaging taped and reeled
Standard Lieferform gegurtet auf Rolle

Maximum ratings (T_A = 25˚C) **Grenzwerte (T_A = 25˚C)**

			BSS 64
Collector-Emitter-voltage	B open	V_{CE0}	80 V
Collector-Base-voltage	E open	V_{CB0}	120 V
Emitter-Base-voltage	C open	V_{EB0}	5 V
Power dissipation – Verlustleistung		P_{tot}	250 mW [1])
Collector current – Kollektorstrom (dc)		I_C	100 mA
Peak Collector current – Kollektor-Spitzenstrom		I_{CM}	250 mA
Peak Base current – Basis-Spitzenstrom		I_{BM}	100 mA
Junction temp. – Sperrschichttemperatur		T_j	150˚C
Storage temperature – Lagerungstemperatur		T_S	- 65…+ 150˚C

Characteristics (T_j = 25˚C) **Kennwerte (T_j = 25˚C)**

		Min.	Typ.	Max.
Collector-Base cutoff current – Kollektorreststrom				
I_E = 0, V_{CB} = 90 V	I_{CB0}	–	–	100 nA
I_E = 0, V_{CB} = 90 V, T_j = 150˚C	I_{CB0}	–	–	50 µA
Emitter-Base cutoff current – Emitterreststrom				
I_C = 0, V_{EB} = 5 V	I_{EB0}	–	1 nA	200 nA
Collector saturation volt. – Kollektor-Sättigungsspg. [1])				
I_C = 4 mA, I_B = 0.4 mA	V_{CEsat}	–	–	150 mV
I_C = 50 mA, I_B = 15 mA	V_{CEsat}	–	–	200 mV

[1]) Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluß

Characteristics (T_j = 25˚C) **Kennwerte (T_j = 25˚C)**

		Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis [1]				
V_{CE} = 1 V, I_C = 1 mA	h_{FE}	–	60	–
V_{CE} = 1 V, I_C = 10 mA	h_{FE}	20	80	–
V_{CE} = 1 V, I_C = 20 mA	h_{FE}	–	55	–
Gain-Bandwidth Product – Transitfrequenz				
V_{CE} = 5 V, I_C = 25 mA, f = 100 MHz	f_T	60 MHz	105 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität				
V_{CB} = 10 V, I_E = i_e = 0, f = 1 MHz	C_{CB0}	–	3 pF	–
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R_{thA}			420 K/W [2]
Recommended complementary PNP transistors Empfohlene komplementäre PNP-Transistoren			BSS 63	

Marking - Stempelung	BSS 64 = AM

[1] Tested with pulses t_p = 300 µs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%
[2] Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluß